

Features

- $V_{DS} = 60V$ $I_D = 12A$
 $R_{DS(ON)} < 85 \text{ m}\Omega @ V_{GS} = 10V$

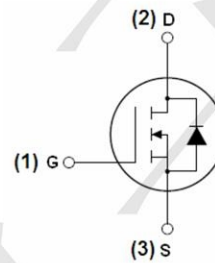
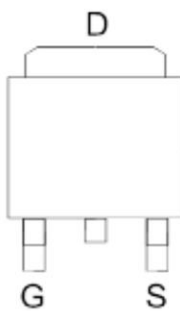
Application

- Battery protection
- Load switch
- Uninterruptible power supply

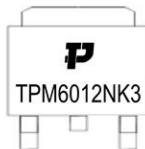
Package and Pin Configuration

(TO-252-3L)

Top View



Marking:



Absolute Maximum Ratings ($T_C = 25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	60	V
V_{GS}	Gate-Source Voltage	± 20	V
$I_D @ T_C = 25^\circ\text{C}$	Continuous Drain Current, $V_{GS} @ 10V^1$	12	A
$I_D @ T_C = 100^\circ\text{C}$	Continuous Drain Current, $V_{GS} @ 10V^1$	10	A
$I_D @ T_A = 25^\circ\text{C}$	Continuous Drain Current, $V_{GS} @ 10V^1$	5	A
$I_D @ T_A = 70^\circ\text{C}$	Continuous Drain Current, $V_{GS} @ 10V^1$	4	A
I_{DM}	Pulsed Drain Current ²	47	A
EAS	Single Pulse Avalanche Energy ³	22	mJ
I_{AS}	Avalanche Current	21	A
$P_D @ T_C = 25^\circ\text{C}$	Total Power Dissipation ⁴	31.3	W
$P_D @ T_A = 25^\circ\text{C}$	Total Power Dissipation ⁴	2	W
T_{STG}	Storage Temperature Range	-55 to 150	$^\circ\text{C}$
T_J	Operating Junction Temperature Range	-55 to 150	$^\circ\text{C}$
$R_{\theta JA}$	Thermal Resistance Junction-ambient ¹	62	$^\circ\text{C/W}$
$R_{\theta JC}$	Thermal Resistance Junction-Case ¹	4	$^\circ\text{C/W}$

Electrical Characteristics ($T_A=25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=250\mu A$	60	---	---	V
$\Delta BV_{DSS}/\Delta T_J$	BVDSS Temperature Coefficient	Reference to $25^\circ\text{C}, I_D=1\text{mA}$	---	0.044	---	$V/^\circ\text{C}$
$R_{DS(ON)}$	Static Drain-Source On-Resistance ²	$V_{GS}=10V, I_D=12A$	---	65	85	m Ω
		$V_{GS}=4.5V, I_D=7A$	---	80	100	
$V_{GS(th)}$	Gate Threshold Voltage		1.0	---	2.5	V
$\Delta V_{GS(th)}$	$V_{GS(th)}$ Temperature Coefficient	$V_{GS}=V_{DS}, I_D=250\mu A$	---	-4.8	---	$\text{mV}/^\circ\text{C}$
I_{DSS}	Drain-Source Leakage Current	$V_{DS}=48V, V_{GS}=0V, T_J=25^\circ\text{C}$	---	---	1	μA
		$V_{DS}=48V, V_{GS}=0V, T_J=55^\circ\text{C}$	---	---	5	
I_{GSS}	Gate-Source Leakage Current	$V_{GS}=\pm 20V, V_{DS}=0V$	---	---	± 100	nA
g_{fs}	Forward Transconductance	$V_{DS}=5V, I_D=10A$	---	25.3	---	S
R_g	Gate Resistance	$V_{DS}=0V, V_{GS}=0V, f=1\text{MHz}$	---	2.5	---	Ω
Q_g	Total Gate Charge (10V)		---	19	---	nC
Q_{gs}	Gate-Source Charge	$V_{DS}=48V, V_{GS}=10V, I_D=12A$	---	2.5	---	
Q_{gd}	Gate-Drain Charge		---	5	---	
$T_{d(on)}$	Turn-On Delay Time		---	2.8	---	ns
T_r	Rise Time	$V_{DD}=30V, V_{GS}=10V, R_G=3.3$	---	16.6	---	
$T_{d(off)}$	Turn-Off Delay Time	$I_D=12A$	---	21.2	---	
T_f	Fall Time		---	5.6	---	
C_{iss}	Input Capacitance		---	560	---	pF
C_{oss}	Output Capacitance	$V_{DS}=15V, V_{GS}=0V, f=1\text{MHz}$	---	65	---	
C_{rss}	Reverse Transfer Capacitance		---	46	---	
I_S	Continuous Source Current ^{1,6}	$V_G=V_D=0V, \text{Force Current}$	---	---	12	A
I_{SM}	Pulsed Source Current ^{2,6}		---	---	47	A
V_{SD}	Diode Forward Voltage ²	$V_{GS}=0V, I_S=1A, T_J=25^\circ\text{C}$	---	---	1.2	V
t_{rr}	Reverse Recovery Time	$I_F=12A, \quad dI/dt=100A/\mu s$	---	12.2	---	nS
Q_{rr}	Reverse Recovery Charge	$T_J=25^\circ\text{C}$	---	7.3	---	nC

Typical Characteristics

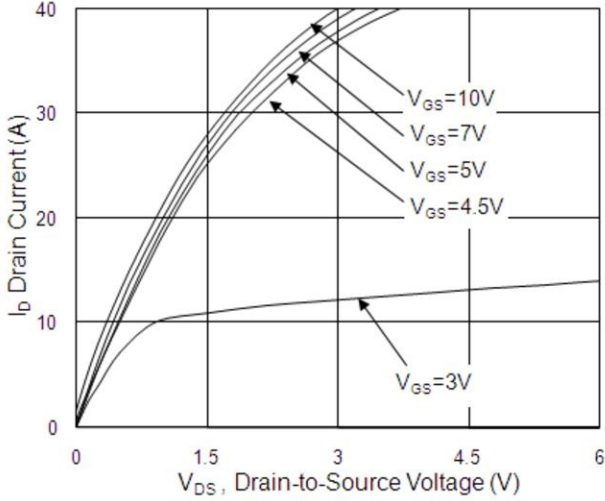


Fig.1 Typical Output Characteristics

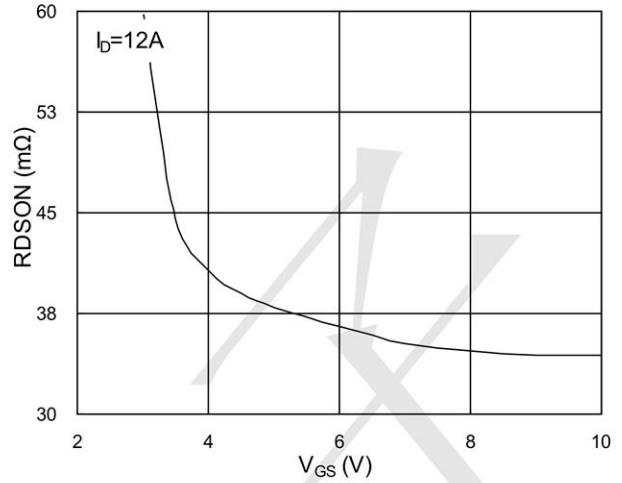


Fig.2 On-Resistance vs. Gate-Source

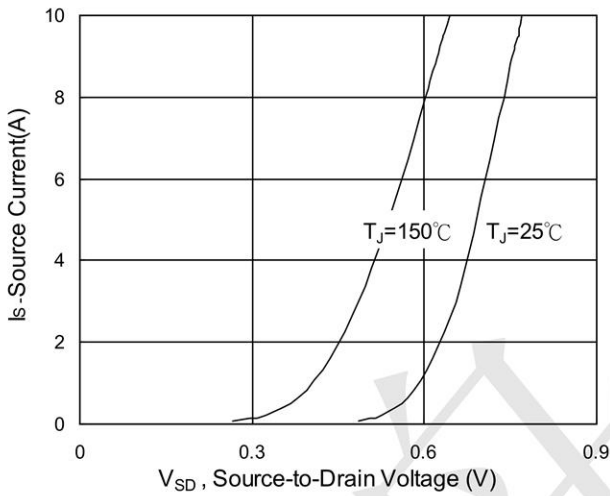


Fig.3 Forward Characteristics Of Reverse

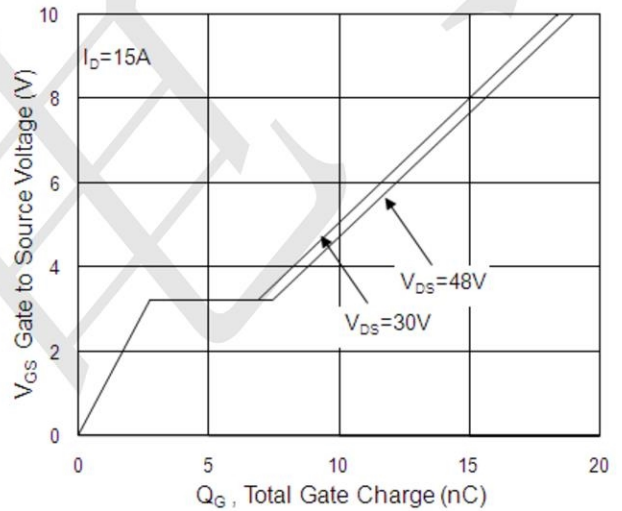


Fig.4 Gate-Charge Characteristics

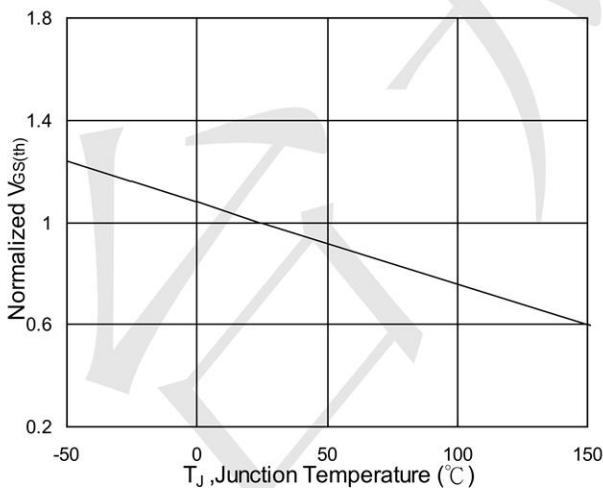


Fig.5 Normalized $V_{GS(th)}$ vs T_J

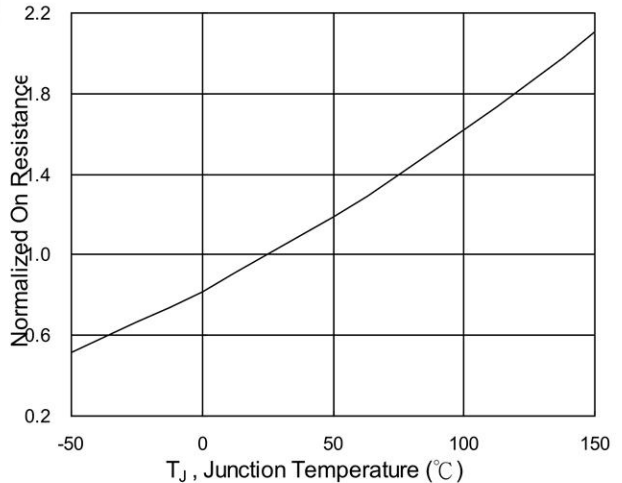


Fig.6 Normalized $R_{DS(on)}$ vs T_J

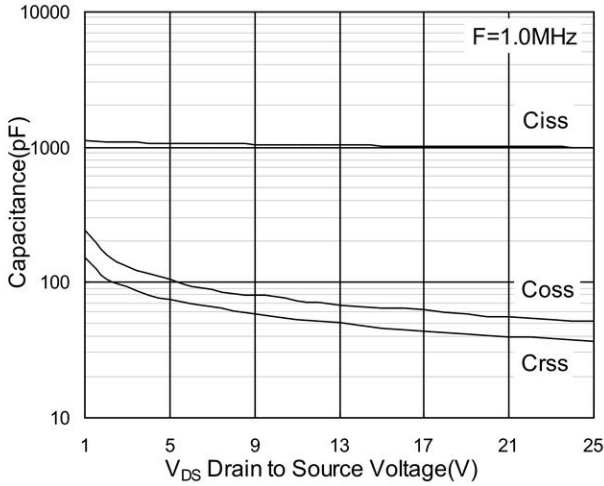


Fig.7 Capacitance

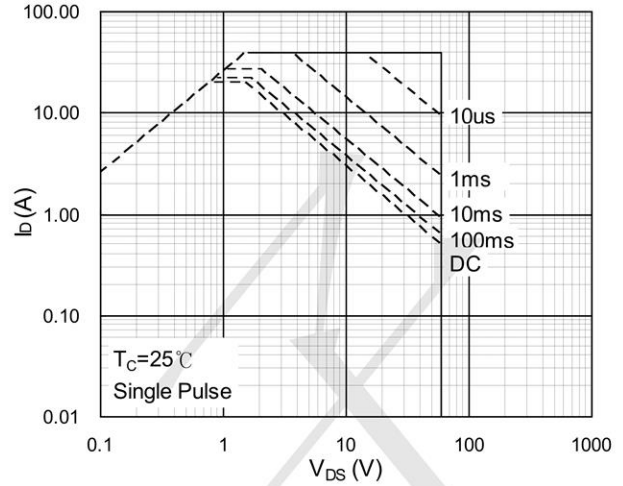


Fig.8 Safe Operating Area

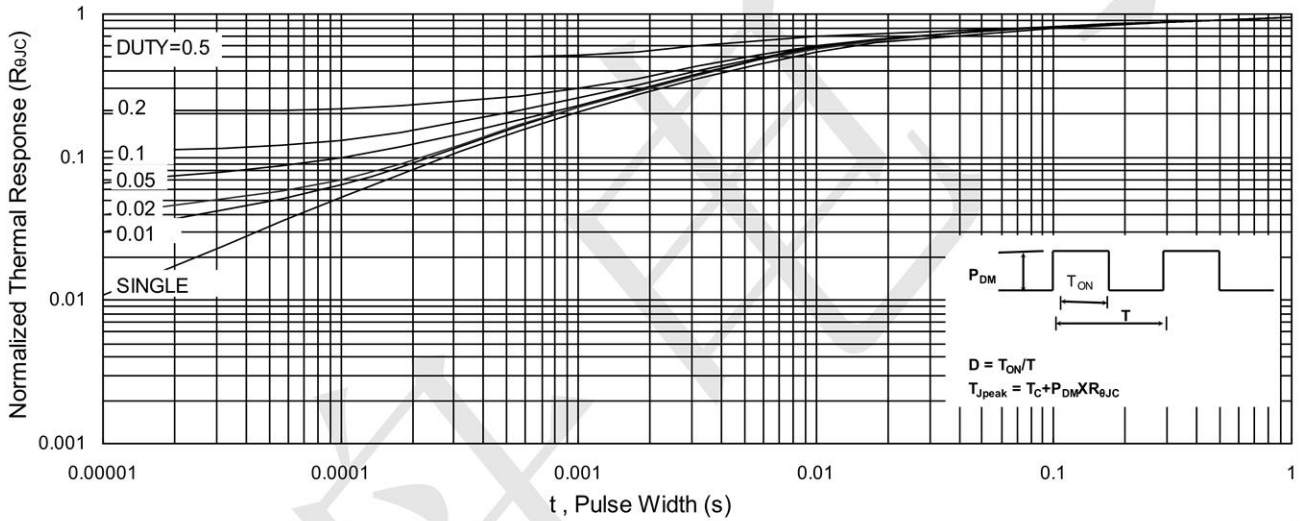


Fig.9 Normalized Maximum Transient Thermal Impedance

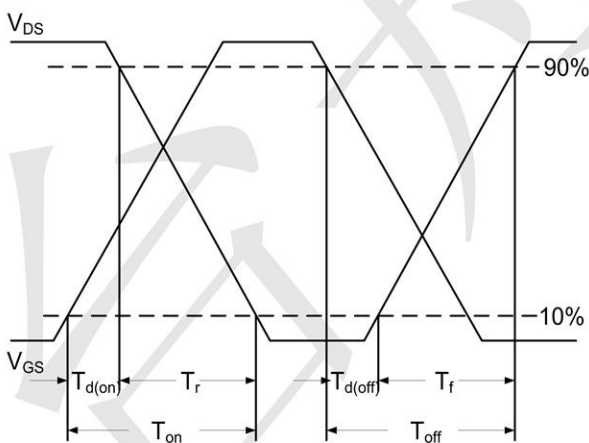


Fig.10 Switching Time Waveform

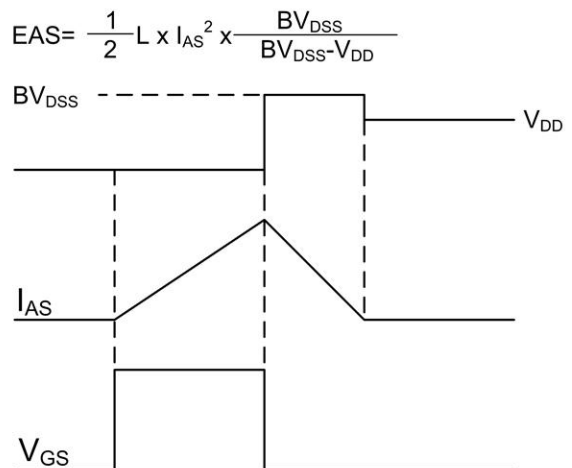
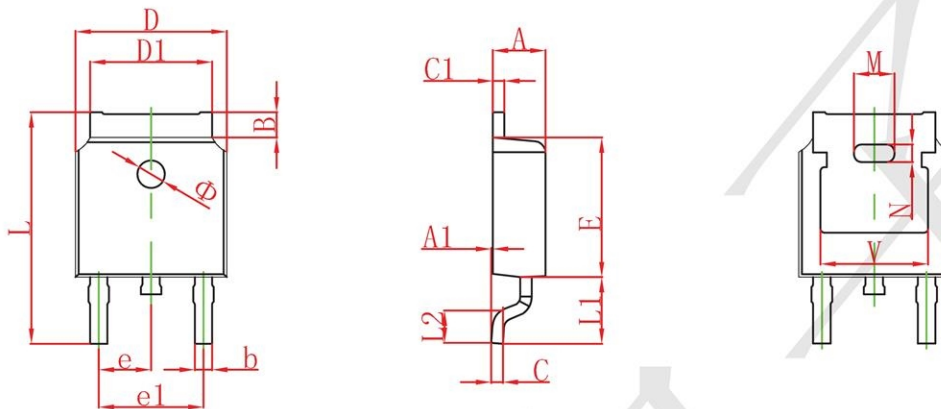


Fig.11 Unclamped Inductive Switching Waveform

TO252 Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	2.200	2.380	0.087	0.094
A1	0.000	0.100	0.000	0.004
B	0.800	1.400	0.031	0.055
b	0.710	0.810	0.028	0.032
c	0.460	0.560	0.018	0.022
c1	0.460	0.560	0.018	0.022
D	6.500	6.700	0.256	0.264
D1	5.130	5.460	0.202	0.215
E	6.000	6.200	0.236	0.244
e	2.286 TYP.		0.090 TYP.	
e1	4.327	4.727	0.170	0.186
M	1.778REF.		0.070REF.	
N	0.762REF.		0.018REF.	
L	9.800	10.400	0.386	0.409
L1	2.9REF.		0.114REF.	
L2	1.400	1.700	0.055	0.067
V	4.830 REF.		0.190 REF.	
Φ	1.100	1.300	0.043	0.051

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